



Dual 10-Bit, 105Msps, +3.3V, Low-Power ADC with Internal Reference and Parallel Outputs

General Description

The MAX1180 is a +3.3V, dual 10-bit, analog-to-digital converter (ADC) featuring fully-differential wideband track-and-hold (T/H) inputs, driving two pipelined, nine-stage ADCs. The MAX1180 is optimized for low-power, high-dynamic performance applications in imaging, instrumentation, and digital communication applications. The MAX1180 operates from a single +2.7V to +3.6V supply, consuming only 413mW, while delivering a typical signal-to-noise ratio (SNR) of 58.5dB at an input frequency of 20MHz and a sampling rate of 105Msps. The T/H driven input stages incorporate 400MHz (-3dB) input amplifiers. The converters may also be operated with single-ended inputs. In addition to low operating power, the MAX1180 features a 2.8mA sleep mode, as well as a 1μA power-down mode to conserve power during idle periods.

An internal +2.048V precision bandgap reference sets the full-scale range of the ADC. A flexible reference structure allows the use of the internal or external reference, if desired for applications requiring increased accuracy or a different input voltage range.

The MAX1180 features parallel, CMOS-compatible three-state outputs. The digital output format is set to two's complement or straight offset binary through a single control pin. The device provides for a separate output power supply of +1.7V to +3.6V for flexible interfacing. The MAX1180 is available in a 7mm × 7mm, 48-pin TQFP package, and is specified for the extended industrial (-40°C to +85°C) temperature range.

Pin-compatible higher and lower speed versions of the MAX1180 are also available. Please refer to the MAX1181 data sheet for 80Msps, the MAX1182 data sheet for 65Msps, the MAX1183 data sheet for 40Msps, and the MAX1184 data sheet for 20Msps. In addition to these speed grades, this family includes a 20Msps multiplexed output version (MAX1185), for which digital data is presented time-interleaved on a single, parallel 10-bit output port.

Applications

High Resolution Imaging
I/Q Channel Digitization
Multichannel IF Undersampling
Instrumentation
Video Application

Functional Diagram appears at end of data sheet.

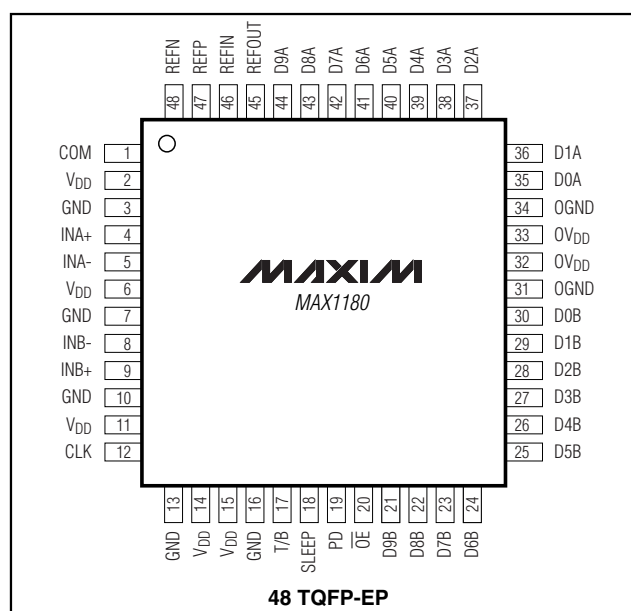
Features

- ◆ Single +3.3V Operation
- ◆ Excellent Dynamic Performance:
58.5dB SNR at $f_{IN} = 20\text{MHz}$
72dB SFDR at $f_{IN} = 20\text{MHz}$
- ◆ SNR Flat within 1dB for $f_{IN} = 202\text{MHz}$ to 100MHz
- ◆ Low Power:
125mA (Normal Operation)
2.8mA (Sleep Mode)
1μA (Shutdown Mode)
- ◆ 0.02dB Gain and 0.25° Phase Matching (typ)
- ◆ Wide $\pm 1\text{Vp-p}$ Differential Analog Input Voltage Range
- ◆ 400MHz, -3dB Input Bandwidth
- ◆ On-Chip +2.048V Precision Bandgap Reference
- ◆ User-Selectable Output Format—Two's Complement or Offset Binary
- ◆ 48-Pin TQFP Package with Exposed Pad for Improved Thermal Dissipation

Ordering Information

PART	TEMP. RANGE	PIN-PACKAGE
MAX1180ECM	-40°C to +85°C	48 TQFP-EP

Pin Configuration



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ABSOLUTE MAXIMUM RATINGS

V _{DD} , OV _{DD} to GND	-0.3V to +3.6V
OGND to GND	-0.3V to +0.3V
INA+, INA-, INB+, INB- to GND	-0.3V to V _{DD}
REFIN, REFOUT, REFP, REFN, CLK, COM to GND	-0.3V to (V _{DD} + 0.3V)
OE, PD, SLEEP, T/B, D9A–D0A, D9B–D0B to OGND	-0.3V to (OV _{DD} + 0.3V)

Continuous Power Dissipation (T _A = +70°C) 48-Pin TQFP (derate 12.5mW/°C above +70°C)	1000mW
Operating Temperature Range	-40°C to +85°C
Junction Temperature	+150°C
Storage Temperature Range	-60°C to +150°C
Lead Temperature (soldering, 10s)	+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

(V_{DD} = +3.3V, OV_{DD} = +2.5V; 0.1μF and 1.0μF capacitors from REFP, REFN, and COM to GND; REFOUT connected to REFIN through a 10kΩ resistor, V_{IN} = 2V_{p-p} (differential w.r.t. COM), C_L = 10pF at digital outputs (Note 5), f_{CLK} = 105.263MHz, T_A = T_{MIN} to T_{MAX}, unless otherwise noted. Typical values are at T_A = +25°C.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
DC ACCURACY						
Resolution			10			Bits
Integral Nonlinearity	INL	f _{IN} = 7.47MHz		±0.75	±2.5	LSB
Differential Nonlinearity	DNL	f _{IN} = 7.47MHz, no missing codes guaranteed	-1	±0.4	+1.5	LSB
Offset Error				< ±1	±1.7	% FS
Gain Error				0	±2	% FS
ANALOG INPUT						
Differential Input Voltage Range	V _{DIFF}	Differential or single-ended inputs		±1.0		V
Common-Mode Input Voltage Range	V _{CM}			V _{DD} /2 ± 0.5		V
Input Resistance	R _{IN}	Switched capacitor load		20		kΩ
Input Capacitance	C _{IN}			5		pF
CONVERSION RATE						
Maximum Clock Frequency	f _{CLK}		105			MHz
Data Latency				5		Clock Cycles
DYNAMIC CHARACTERISTICS (f _{CLK} = 105.263MHz, 4096-point FFT)						
Signal-to-Noise Ratio	SNR	f _{INA} or B = 7.47MHz, T _A = +25°C		59		dB
		f _{INA} or B = 20MHz, T _A = +25°C	55	58.5		
		f _{INA} or B = 50.078MHz (Note 1)		58		
Signal-to-Noise and Distortion (up to 5 th harmonic)	SINAD	f _{INA} or B = 7.47MHz, T _A = +25°C		58.2		dB
		f _{INA} or B = 20MHz, T _A = +25°C	54.7	58.1		
		f _{INA} or B = 50.078MHz (Note 1)		57.6		
Spurious-Free Dynamic Range	SFDR	f _{INA} or B = 7.47MHz, T _A = +25°C		72		dBc
		f _{INA} or B = 20MHz, T _A = +25°C	60	72		
		f _{INA} or B = 50.078MHz, (Note 1)		70		
Third-Harmonic Distortion	HD3	f _{INA} or B = 7.47MHz		-75		dBc
		f _{INA} or B = 20MHz		-75		
		f _{INA} or B = 50.078MHz (Note 1)		-73		

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ELECTRICAL CHARACTERISTICS (continued)

($V_{DD} = +3.3V$, $OV_{DD} = +2.5V$; 0.1 μF and 1.0 μF capacitors from REFP, REFN, and COM to GND; REFOUT connected to REFIN through a 10k Ω resistor, $V_{IN} = 2V_{p-p}$ (differential w.r.t. COM), $C_L = 10pF$ at digital outputs (Note 5), $f_{CLK} = 105.263MHz$, $T_A = T_{MIN}$ to T_{MAX} , unless otherwise noted. Typical values are at $T_A = +25^\circ C$.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Intermodulation Distortion (first five odd-order IMDs)	IMD	f_{INA} or B = 38.055MHz at -6.5dB FS f_{INA} or B = 42.926MHz at -6.5dB FS (Note 2)		-74		dBc
Total Harmonic Distortion (first five harmonics)	THD	f_{INA} or B = 7.47MHz, $T_A = +25^\circ C$		-71		dBc
		f_{INA} or B = 20MHz, $T_A = +25^\circ C$		-70	-59	
		f_{INA} or B = 50.078MHz, (Note 1)		-69		
Small-Signal Bandwidth		Input at -20dB FS, differential inputs		500		MHz
Full-Power Bandwidth	FPBW	Input at -0.5dB FS, differential inputs		400		MHz
Aperture Delay	t_{AD}			1		ns
Aperture Jitter	t_{AJ}			2		psRMS
Overdrive Recovery Time		For 1.5 $\times$ full-scale input		2		ns
Differential Gain				± 1		%
Differential Phase				± 0.25		degrees
Output Noise		INA+ = INA- = INB+ = INB- = COM		0.2		LSBRMS
INTERNAL REFERENCE						
Reference Output Voltage	REFOUT			2.048 $\pm 3\%$		V
Reference Temperature Coefficient	T_{CREF}			60		ppm/ $^\circ C$
Load Regulation				1.25		mV/mA
BUFFERED EXTERNAL REFERENCE ($V_{REFIN} = +2.048V$)						
REFIN Input Voltage	V_{REFIN}			2.048		V
Positive Reference Output Voltage	V_{REFP}			2.162		V
Negative Reference Output Voltage	V_{REFN}			1.138		V
Differential Reference Output Voltage Range	ΔV_{REF}	$\Delta V_{REF} = V_{REFP} - V_{REFN}$	0.98	1.024	1.07	V
REFIN Resistance	R_{REFIN}			>50		M Ω
Maximum REFP, COM Source Current	I_{SOURCE}			5		mA
Maximum REFP, COM Sink Current	I_{SINK}			-250		μA
Maximum REFN Source Current	I_{SOURCE}			250		μA
Maximum REFN Sink Current	I_{SINK}			-5		mA

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ELECTRICAL CHARACTERISTICS (continued)

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PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
UNBUFFERED EXTERNAL REFERENCE ($V_{REFIN} = AGND$, reference voltage applied to REFP, REFN, and COM)						
REFP, REFN Input Resistance	R_{REFP}, R_{REFN}	Measured between REFP and COM and REFN and COM		4		k Ω
Differential Reference Input Voltage Range	ΔV_{REF}	$\Delta V_{REF} = V_{REFP} - V_{REFN}$		1.024 $\pm 10\%$		V
COM Input Voltage Range	V_{COM}			$V_{DD}/2$ $\pm 10\%$		V
REFP Input Voltage	V_{REFP}			$V_{COM} + \Delta V_{REF}/2$		V
REFN Input Voltage	V_{REFN}			$V_{COM} - \Delta V_{REF}/2$		V
DIGITAL INPUTS (CLK, PD, $\overline{OE}$, SLEEP, T/B)						
Input High Threshold	V_{IH}	CLK		0.8 x V_{DD}		V
		PD, $\overline{OE}$, SLEEP, T/B		0.8 x OV_{DD}		
Input Low Threshold	V_{IL}	CLK		0.2 x V_{DD}		V
		PD, $\overline{OE}$, SLEEP, T/B		0.2 x OV_{DD}		
Input Hysteresis	V_{HYST}			0.1		V
Input Leakage	I_{IH}	$V_{IH} = OV_{DD}$ or V_{DD} (CLK)		± 5		μA
	I_{IL}	$V_{IL} = 0$		± 5		
Input Capacitance	C_{IN}			5		pF
DIGITAL OUTPUTS (D9A–D0A, D9B–D0B)						
Output Voltage Low	V_{OL}	$I_{SINK} = -200\mu A$			0.2	V
Output Voltage High	V_{OH}	$I_{SOURCE} = 200\mu A$		$OV_{DD} - 0.2$		V
Three-State Leakage Current	I_{LEAK}	$\overline{OE} = OV_{DD}$		± 10		μA
Three-State Output Capacitance	C_{OUT}	$\overline{OE} = OV_{DD}$		5		pF
POWER REQUIREMENTS						
Analog Supply Voltage Range	V_{DD}		2.7	3.3	3.6	V
Output Supply Voltage Range	OV_{DD}		1.7	2.5	3.6	V
Analog Supply Current	I_{VDD}	Operating, f_{INA} or B = 20MHz at -0.5dB FS		125	155	mA
		Sleep mode		2.8		
		Shutdown, clock idle, PD = $\overline{OE} = OV_{DD}$		1	15	μA

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ELECTRICAL CHARACTERISTICS (continued)

($V_{DD} = +3.3V$, $OV_{DD} = +2.5V$; 0.1 μF and 1.0 μF capacitors from REFP, REFN, and COM to GND; REFOUT connected to REFIN through a 10k Ω resistor, $V_{IN} = 2V_{p-p}$ (differential w.r.t. COM), $C_L = 10pF$ at digital outputs (Note 5), $f_{CLK} = 105.263MHz$, $T_A = T_{MIN}$ to T_{MAX} , unless otherwise noted. Typical values are at $T_A = +25^\circ C$.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Output Supply Current	I _{OVDD}	Operating, C _L = 15pF , f _{INA} or B = 20MHz at -0.5dB FS	15			mA
		Sleep mode	100			μA
		Shutdown, clock idle, PD = $\overline{OE}$ = OV _{DD}	2	10		μA
Power Dissipation	PDISS	Operating, f _{INA} or B = 20MHz at -0.5dB FS	413	511		mW
		Sleep mode	9.2			μW
		Shutdown, clock idle, PD = $\overline{OE}$ = OV _{DD}	3	50		
Power-Supply Rejection Ratio	PSRR	Offset	±0.2			mV/V
		Gain	±0.1			%/V
TIMING CHARACTERISTICS						
CLK Rise to Output Data Valid	t _{DO}	Figure 3 (Note 3)	5		8	ns
Output Enable Time	t _{ENABLE}	Figure 4	10			ns
Output Disable Time	t _{DISABLE}	Figure 4	1.5			ns
CLK Pulse Width High	t _{CH}	Figure 3, clock period: 9.5ns	4.75 ±1.5			ns
CLK Pulse Width Low	t _{CL}	Figure 3, clock period: 9.5ns	4.75 ±1.5			ns
Wake-Up Time	t _{WAKE}	Wakeup from sleep mode (Note 4)	0.18			μs
		Wakeup from shutdown (Note 4)	1.5			
CHANNEL-TO-CHANNEL MATCHING						
Crosstalk		f _{INA} or B = 20MHz at -0.5dB FS	-70			dB
Gain Matching		f _{INA} or B = 20MHz at -0.5dB FS	0.02	±0.2		dB
Phase Matching		f _{INA} or B = 20MHz at -0.5dB FS	0.25			degrees

Note 1: SNR, SINAD, THD, SFDR, and HD3 are based on an analog input voltage of -0.5dB FS, referenced to a +1.024V full-scale input voltage range.

Note 2: Intermodulation distortion is the total power of the intermodulation products relative to the individual carrier. This number is 6dB or better, if referenced to the two-tone envelope.

Note 3: Digital outputs settle to V_{IH} , V_{IL} . Parameter guaranteed by design.

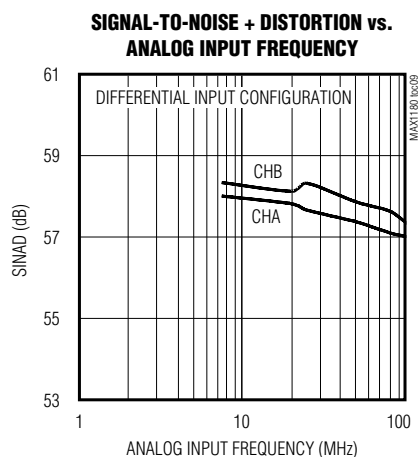
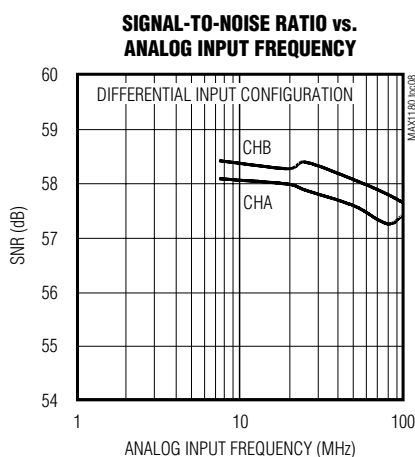
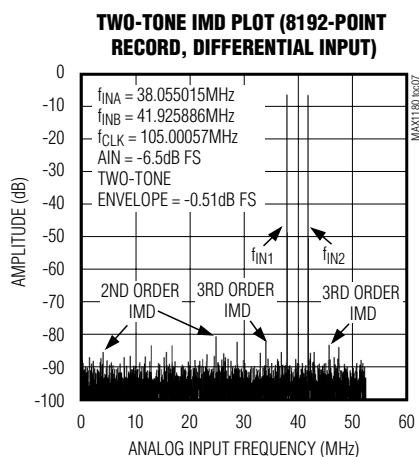
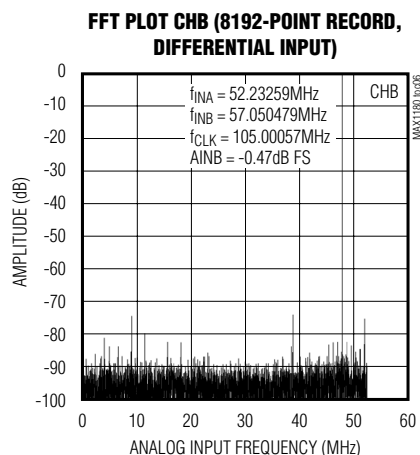
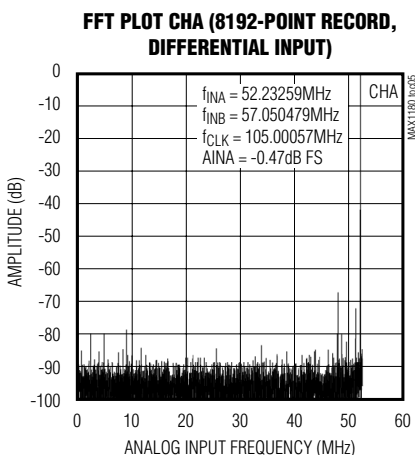
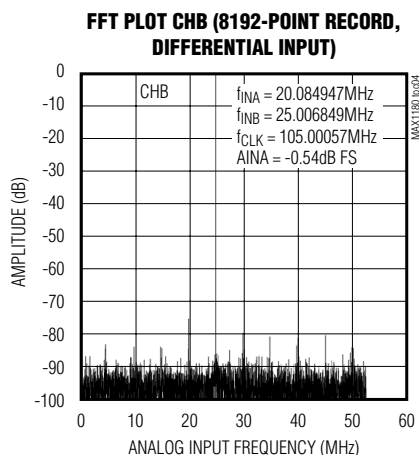
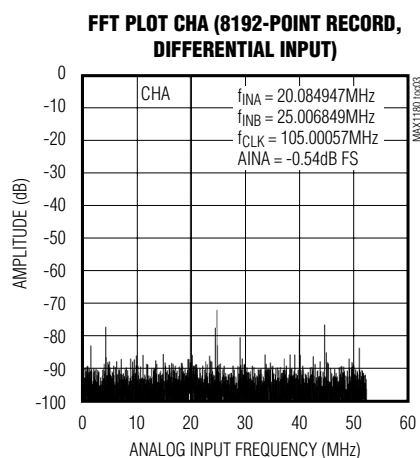
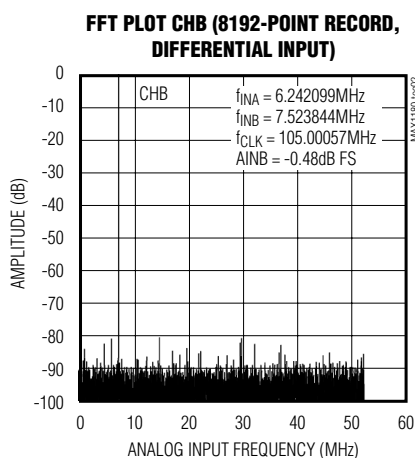
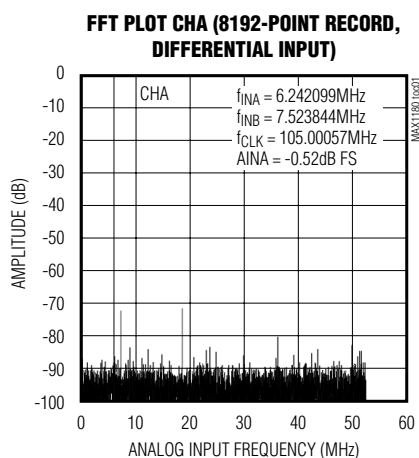
Note 4: With REFIN driven externally, REFP, COM, and REFN are left floating while powered down.

Note 5: Equivalent dynamic performance is obtainable over full OV_{DD} range with reduced C_L .

Dual 10-Bit, 105Mps, +3.3V, Low-Power ADC with Internal Reference and Parallel Outputs

Typical Operating Characteristics

($V_{DD} = +3.3V$, $OV_{DD} = +2.5V$, internal reference, differential input at $-0.5dB$ FS, $f_{CLK} = 105.0005678MHz$, $C_L \approx 10pF$, $T_A = +25^\circ C$, unless otherwise noted.)



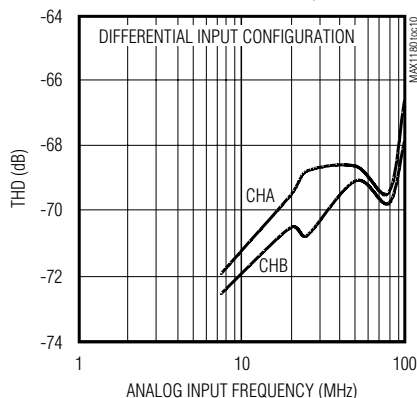
Dual 10-Bit, 105Mps, +3.3V, Low-Power ADC with Internal Reference and Parallel Outputs

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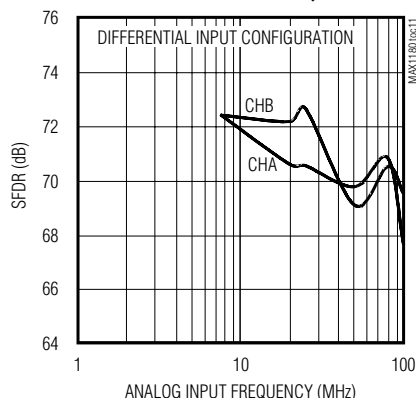
Typical Operating Characteristics (continued)

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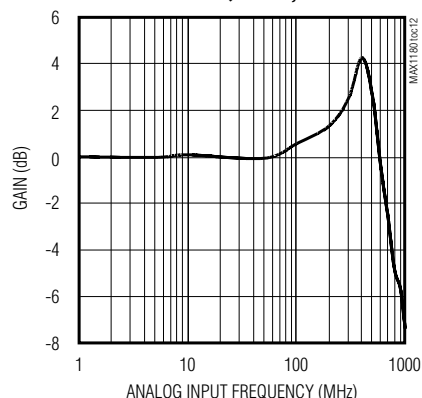
TOTAL HARMONIC DISTORTION vs. ANALOG INPUT FREQUENCY



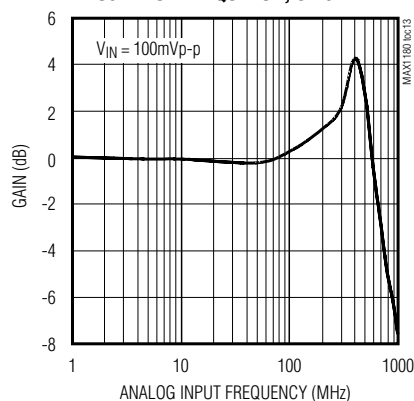
SPURIOUS-FREE DYNAMIC RANGE vs. ANALOG INPUT FREQUENCY



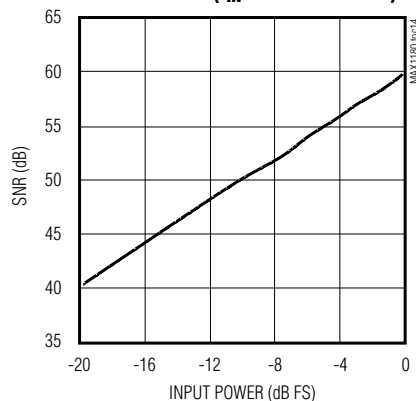
FULL-POWER INPUT BANDWIDTH vs. ANALOG INPUT FREQUENCY, SINGLE-ENDED



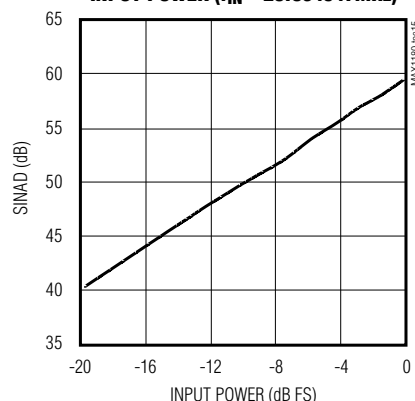
SMALL-SIGNAL INPUT BANDWIDTH vs. ANALOG INPUT FREQUENCY, SINGLE-ENDED



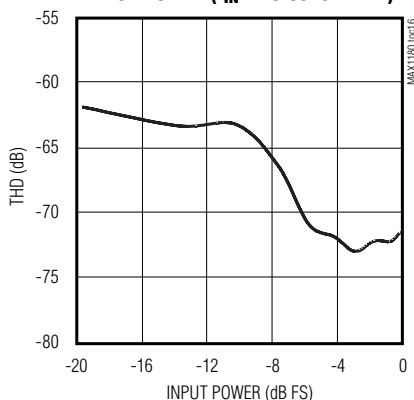
SIGNAL-TO-NOISE RATIO vs. INPUT POWER ($f_{IN} = 20.084947MHz$)



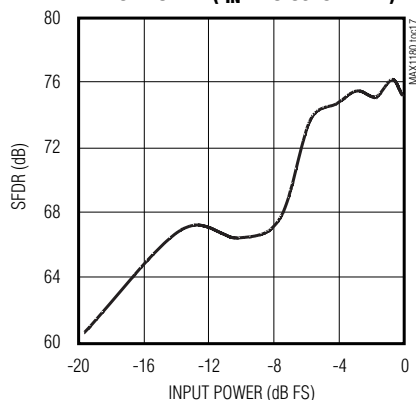
SIGNAL-TO-NOISE + DISTORTION vs. INPUT POWER ($f_{IN} = 20.084947MHz$)



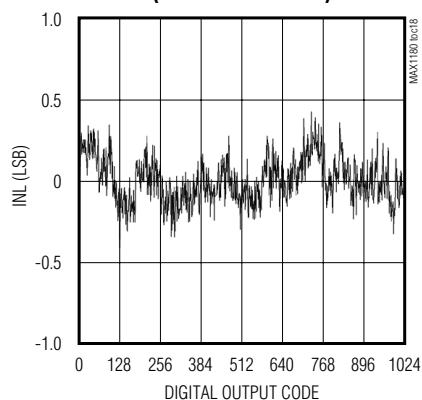
TOTAL HARMONIC DISTORTION vs. INPUT POWER ($f_{IN} = 20.084947MHz$)



SPURIOUS-FREE DYNAMIC RANGE vs. INPUT POWER ($f_{IN} = 20.084947MHz$)



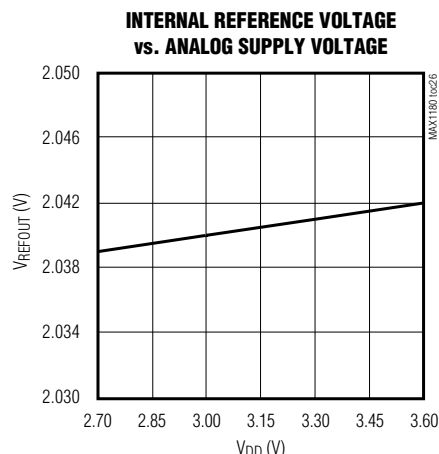
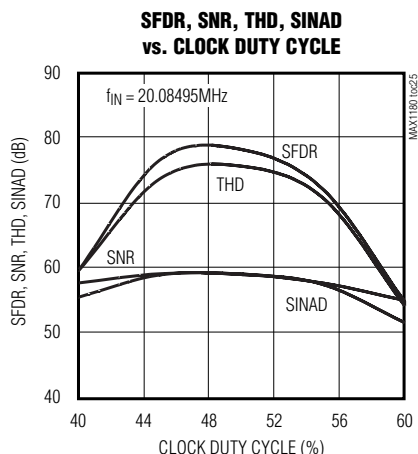
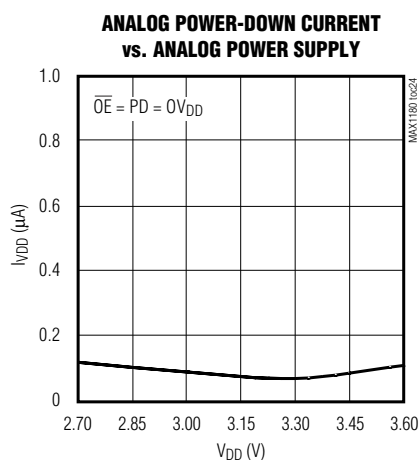
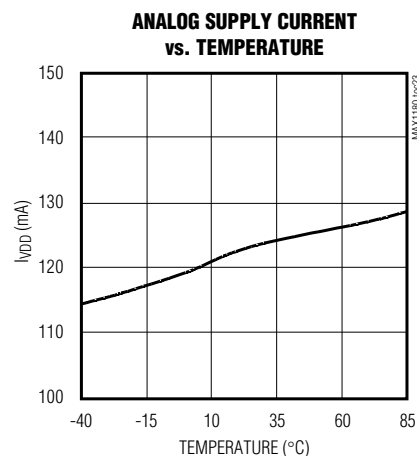
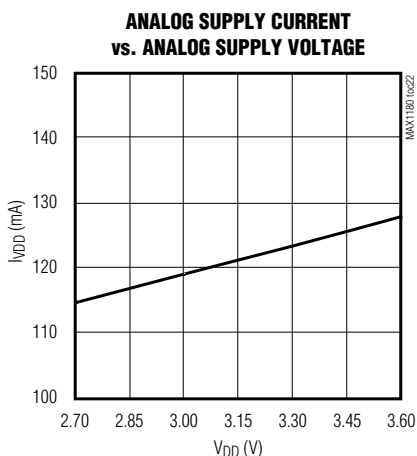
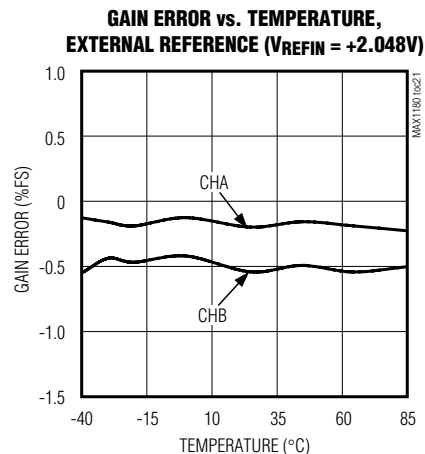
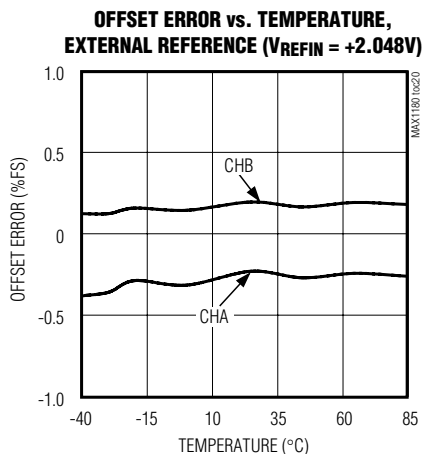
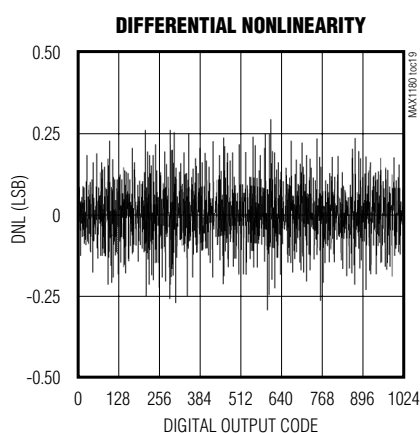
INTEGRAL NONLINEARITY (BEST ENDPOINT FIT)



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Typical Operating Characteristics (continued)

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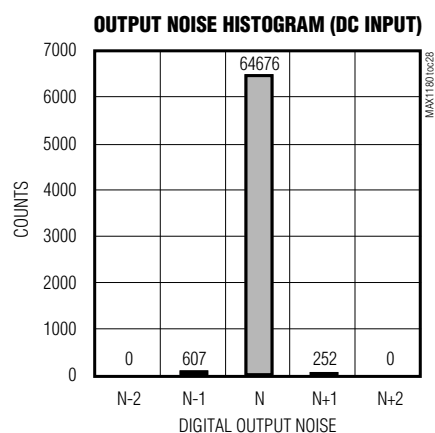
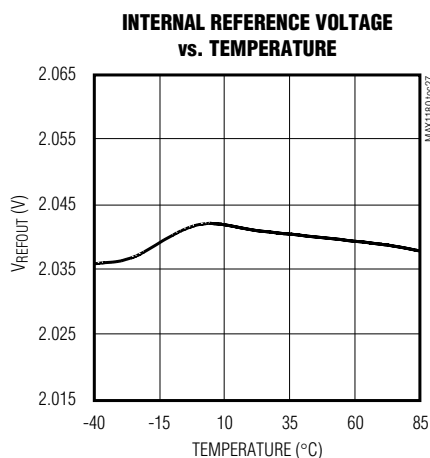


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Typical Operating Characteristics (continued)

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Pin Description

PIN	NAME	FUNCTION
1	COM	Common-Mode Voltage Input/Output. Bypass to GND with a $\geq 0.1\mu F$ capacitor.
2, 6, 11, 14, 15	V_{DD}	Analog Supply Voltage. Bypass to GND with a capacitor combination of $2.2\mu F$ in parallel with $0.1\mu F$.
3, 7, 10, 13, 16	GND	Analog Ground
4	INA+	Channel A Positive Analog Input. For single-ended operation, connect signal source to INA+.
5	INA-	Channel A Negative Analog Input. For single-ended operation, connect INA- to COM.
8	INB-	Channel B Negative Analog Input. For single-ended operation, connect INB- to COM.
9	INB+	Channel B Positive Analog Input. For single-ended operation, connect signal source to INB+.
12	CLK	Converter Clock Input
17	T/B	T/B selects the ADC digital output format. High: Two's complement. Low: Straight offset binary.
18	SLEEP	Sleep Mode Input. High: Deactivates the two ADCs, but leaves the reference bias circuit active. Low: Normal operation.
19	PD	Power-Down Input. High: Power-down mode Low: Normal operation
20	$\overline{OE}$	Output Enable Input. High: Digital outputs disabled Low: Digital outputs enabled

Dual 10-Bit, 105Msps, +3.3V, Low-Power ADC with Internal Reference and Parallel Outputs

Pin Description (continued)

PIN	NAME	FUNCTION
21	D9B	Three-State Digital Output, Bit 9 (MSB), Channel B
22	D8B	Three-State Digital Output, Bit 8, Channel B
23	D7B	Three-State Digital Output, Bit 7, Channel B
24	D6B	Three-State Digital Output, Bit 6, Channel B
25	D5B	Three-State Digital Output, Bit 5, Channel B
26	D4B	Three-State Digital Output, Bit 4, Channel B
27	D3B	Three-State Digital Output, Bit 3, Channel B
28	D2B	Three-State Digital Output, Bit 2, Channel B
29	D1B	Three-State Digital Output, Bit 1, Channel B
30	D0B	Three-State Digital Output, Bit 0 (LSB), Channel B
31, 34	OGND	Output Driver Ground
32, 33	OVDD	Output Driver Supply Voltage. Bypass to OGND with a capacitor combination of 2.2 μ F in parallel with 0.1 μ F.
35	D0A	Three-State Digital Output, Bit 0 (LSB), Channel A
36	D1A	Three-State Digital Output, Bit 1, Channel A
37	D2A	Three-State Digital Output, Bit 2, Channel A
38	D3A	Three-State Digital Output, Bit 3, Channel A
39	D4A	Three-State Digital Output, Bit 4, Channel A
40	D5A	Three-State Digital Output, Bit 5, Channel A
41	D6A	Three-State Digital Output, Bit 6, Channel A
42	D7A	Three-State Digital Output, Bit 7, Channel A
43	D8A	Three-State Digital Output, Bit 8, Channel A
44	D9A	Three-State Digital Output, Bit 9 (MSB), Channel A
45	REFOUT	Internal Reference Voltage Output. May be connected to REFIN through a resistor or a resistor divider.
46	REFIN	Reference Input. $V_{REFIN} = 2 \times (V_{REFP} - V_{REFN})$. Bypass to GND with a >1nF capacitor.
47	REFP	Positive Reference Input/Output. Conversion range is $\pm(V_{REFP} - V_{REFN})$. Bypass to GND with a > 0.1 μ F capacitor.
48	REFN	Negative Reference Input/Output. Conversion range is $\pm(V_{REFP} - V_{REFN})$. Bypass to GND with a > 0.1 μ F capacitor.

Dual 10-Bit, 105Mps, +3.3V, Low-Power ADC with Internal Reference and Parallel Outputs

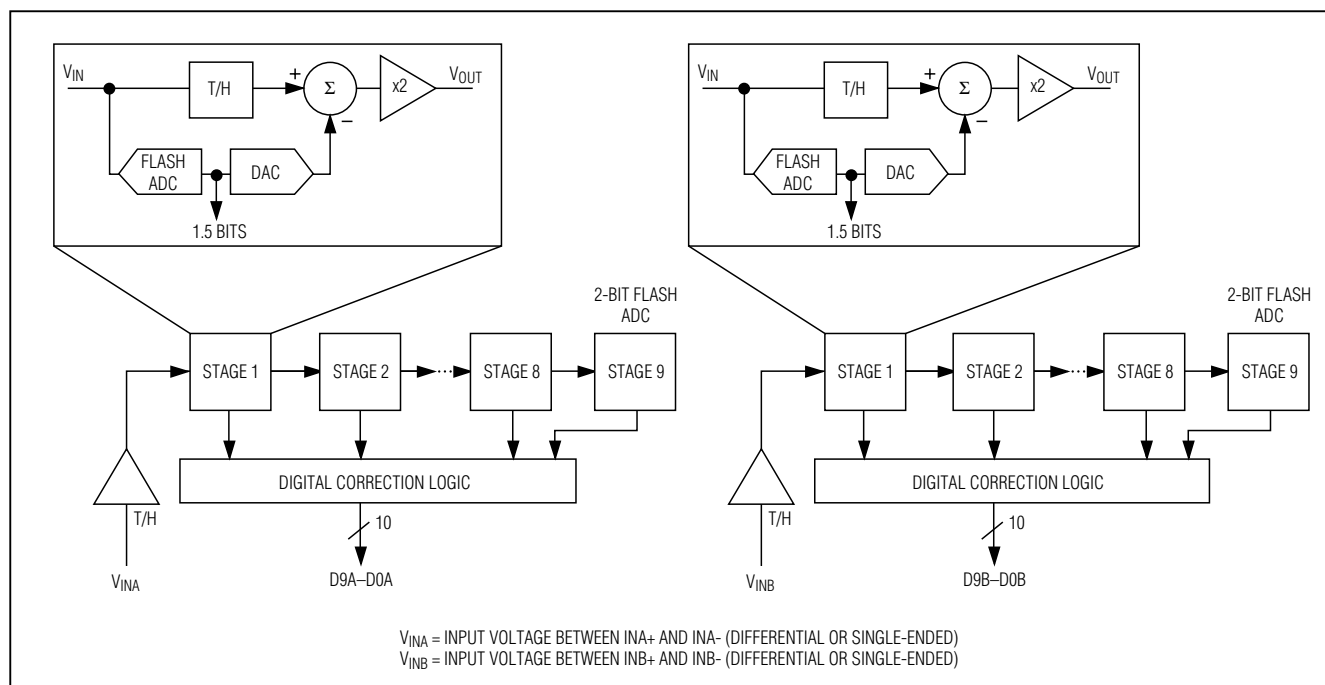


Figure 1. Pipelined Architecture—Stage Blocks

Detailed Description

The MAX1180 uses a nine-stage, fully-differential pipelined architecture (Figure 1), that allows for high-speed conversion while minimizing power consumption. Samples taken at the inputs move progressively through the pipeline stages every half clock cycle. Counting the delay through the output latch, the clock-cycle latency is five clock cycles.

1.5-bit (two-comparator) flash ADCs convert the held-input voltages into a digital code. The digital-to-analog converters (DACs) convert the digitized results back into analog voltages, which are then subtracted from the original held-input signals. The resulting error signals are then multiplied by two and the residues are passed along to the next pipeline stages where the process is repeated until the signals have been processed by all nine stages. Digital error correction compensates for ADC comparator offsets in each of these pipeline stages and ensures no missing codes.

Input Track-and-Hold (T/H) Circuits

Figure 2 displays a simplified functional diagram of the input track-and-hold (T/H) circuits in both track-and-hold mode. In track mode, switches S1, S2a, S2b, S4a, S4b, S5a and S5b are closed. The fully-differential circuits sample the input signals onto the two capacitors

(C2a and C2b) through switches S4a and S4b. S2a and S2b set the common mode for the amplifier input, and open simultaneously with S1, sampling the input waveform. Switches S4a and S4b are then opened before switches S3a and S3b, connect capacitors C1a and C1b to the output of the amplifier, and switch S4c is closed. The resulting differential voltages are held on capacitors C2a and C2b. The amplifiers are used to charge capacitors C1a and C1b to the same values originally held on C2a and C2b. These values are then presented to the first-stage quantizers and isolate the pipelines from the fast-changing inputs. The wide input bandwidth T/H amplifiers allow the MAX1180 to track-and-sample/hold analog inputs of high frequencies ($> Nyquist$). Both ADC inputs ($INA+$, $INB+$, $INA-$, and $INB-$) can be driven either differentially or single-ended. Match the impedance of $INA+$ and $INA-$, as well as $INB+$ and $INB-$, and set the common-mode voltage to midsupply ($V_{DD}/2$) for optimum performance.

Analog Inputs and Reference Configurations

The full-scale range of the MAX1180 is determined by the internally generated voltage difference between $REFP$ ($V_{DD}/2 + V_{REFIN}/4$) and $REFN$ ($V_{DD}/2 - V_{REFIN}/4$). The full-scale range for both on-chip

Dual 10-Bit, 105Msps, +3.3V, Low-Power ADC with Internal Reference and Parallel Outputs

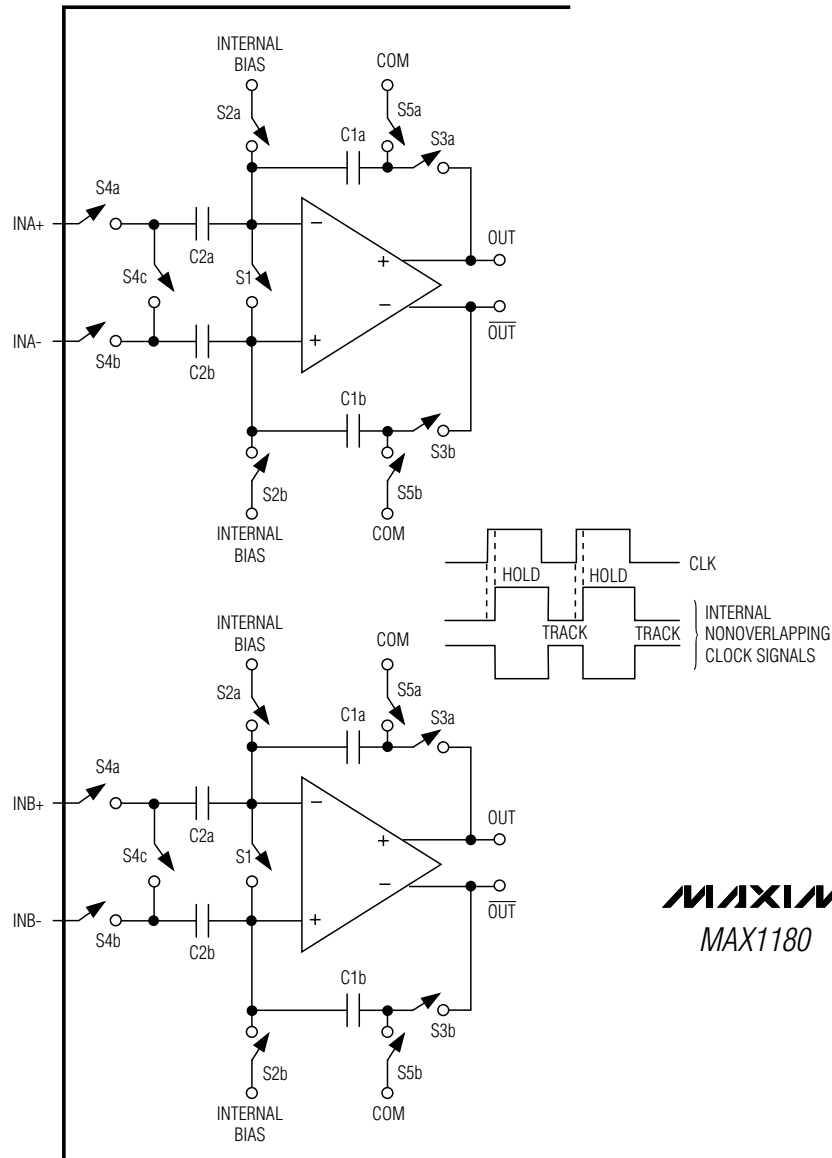


Figure 2. MAX1180 T/H Amplifiers

ADCs is adjustable through the REFIN pin, which is provided for this purpose.

REFOUT, REFP, COM ($V_{DD}/2$), and REFN are internally buffered low-impedance outputs.

The MAX1180 provides three modes of reference operation:

- Internal reference mode
- Buffered external reference mode
- Unbuffered external reference mode

In the internal reference mode, connect the internal reference output REFOUT to REFIN through a resistor (e.g., 10k Ω) or resistor divider, if an application

Dual 10-Bit, 105Mps, +3.3V, Low-Power ADC with Internal Reference and Parallel Outputs

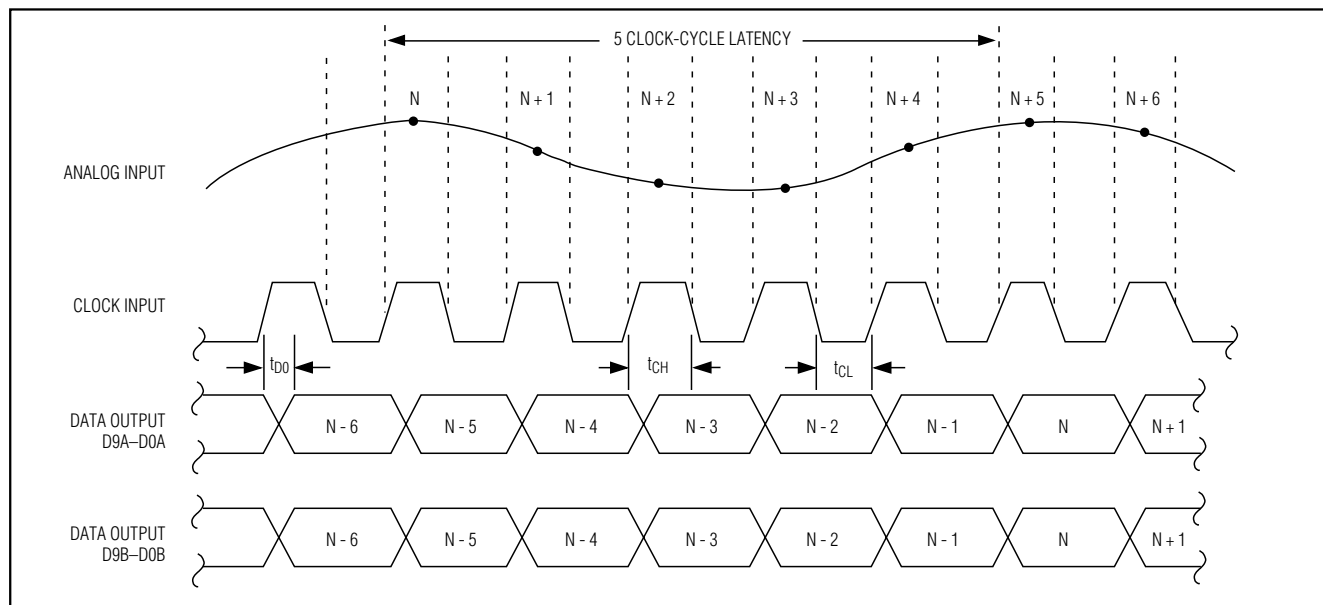


Figure 3. System Timing Diagram

Table 1. MAX1180 Output Codes For Differential Inputs

DIFFERENTIAL INPUT VOLTAGE*	DIFFERENTIAL INPUT	STRAIGHT OFFSET BINARY T/B = 0	TWO'S COMPLEMENT T/B = 1
$V_{REF} \times 511/512$	+FULL SCALE - 1LSB	11 1111 1111	01 1111 1111
$V_{REF} \times 1/512$	+ 1 LSB	10 0000 0001	00 0000 0001
0	Bipolar Zero	10 0000 0000	00 0000 0000
$-V_{REF} \times 1/512$	- 1 LSB	01 1111 1111	11 1111 1111
$-V_{REF} \times 511/512$	-FULL SCALE + 1 LSB	00 0000 0001	10 0000 0001
$-V_{REF} \times 512/512$	-FULL SCALE	00 0000 0000	10 0000 0000

* $V_{REF} = V_{REFP} - V_{REFN}$

requires a reduced full-scale range. For stability and noise filtering purposes, bypass REFIN with a $>10\text{nF}$ capacitor to GND. In internal reference mode, REFOUT, COM, REFP, and REFN become low-impedance outputs.

In the buffered external reference mode, adjust the reference voltage levels externally by applying a stable and accurate voltage at REFIN. In this mode, COM, REFP, and REFN become outputs. REFOUT may be left open or connected to REFIN through a $>10\text{k}\Omega$ resistor.

In the unbuffered external reference mode, connect REFIN to GND. This deactivates the on-chip reference buffers for REFP, COM, and REFN. With their buffers

shut down, these nodes become high impedance and may be driven through separate external reference sources.

Clock Input (CLK)

The MAX1180's CLK input accepts CMOS-compatible clock signals. Since the interstage conversion of the device depends on the repeatability of the rising and falling edges of the external clock, use a clock with low jitter and fast rise and fall times ($< 2\text{ns}$). In particular, sampling occurs on the rising edge of the clock signal, requiring this edge to provide lowest possible jitter. Any significant aperture jitter would limit the SNR performance of the on-chip ADCs as follows:

Dual 10-Bit, 105Msps, +3.3V, Low-Power ADC with Internal Reference and Parallel Outputs

$$\text{SNR}_{\text{dB}} = 20 \times \log_{10} (1 / [2\pi \times f_{\text{IN}} \times t_{\text{AJ}}]),$$

where f_{IN} represents the analog input frequency and t_{AJ} is the time of the aperture jitter.

Clock jitter is especially critical for undersampling applications. The clock input should always be considered as an analog input and routed away from any analog input or other digital signal lines.

The MAX1180 clock input operates with a voltage threshold set to $V_{\text{DD}}/2$. Clock inputs with a duty cycle other than 50%, must meet the specifications for high and low periods as stated in the *Electrical Characteristics*.

System Timing Requirements

Figure 3 depicts the relationship between the clock input, analog input, and data output. The MAX1180 samples at the rising edge of the input clock. Output data for channels A and B is valid on the next rising edge of the input clock. The output data has an internal latency of five clock cycles. Figure 4 also determines the relationship between the input clock parameters and the valid output data on channels A and B.

Digital Output Data, Output Data Format Selection (T/B), Output Enable ($\overline{\text{OE}}$)

All digital outputs, D0A–D9A (Channel A) and D0B–D9B (Channel B), are TTL/CMOS logic-compatible. There is a five clock cycle latency between any particular sample and its corresponding output data. The output coding can be chosen to be either straight offset binary or two's complement (Table 1) controlled by a single pin (T/B). Pull T/B low to select offset binary and high to activate two's complement output coding. The capacitive load on the digital outputs D0A–D9A and D0B–D9B should be kept as low as possible (<15pF), to avoid large digital currents that could feed back into the analog portion of the MAX1180, thereby degrading its dynamic performance. Using buffers on the digital outputs of the ADCs can further isolate the digital outputs from heavy capacitive loads. To further improve the dynamic performance of the MAX1180 small-series resistors (e.g., 100 Ω), add to the digital output paths, close to the MAX1180.

Figure 4 displays the timing relationship between output enable and data output valid, as well as power-down/wake-up and data output valid.

Power-Down (PD) and Sleep (SLEEP) Modes

The MAX1180 offers two power-save modes, sleep and full power-down mode. In sleep mode (SLEEP = 1), only the reference bias circuit is active (both ADCs are

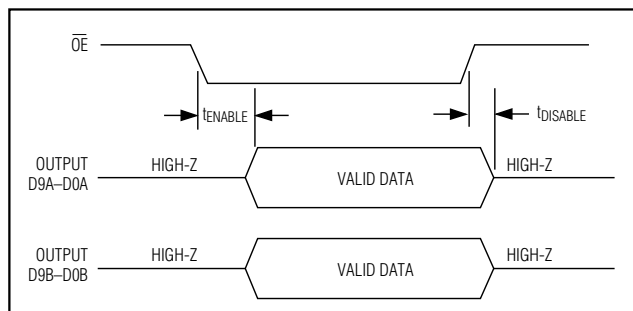


Figure 4. Output Timing Diagram

disabled) and current consumption is reduced to 2.8mA.

To enter full power-down mode, pull PD high. With $\overline{\text{OE}}$ simultaneously low, all outputs are latched at the last value prior to the power-down. Pulling $\overline{\text{OE}}$ high, forces the digital outputs into a high-impedance state.

Applications Information

Figure 5 depicts a typical application circuit containing two single-ended to differential converters. The internal reference provides a $V_{\text{DD}}/2$ output voltage for level-shifting purposes. The input is buffered and then split to a voltage follower and inverter. One lowpass filter per ADC suppresses some of the wideband noise associated with high-speed operational amplifiers. The user may select the R_{ISO} and C_{IN} values to optimize the filter performance to suit a particular application. For the application in Figure 5, a R_{ISO} of 50 Ω is placed before the capacitive load to prevent ringing and oscillation. The 22pF C_{IN} capacitor acts as a small bypassing capacitor.

Using Transformer Coupling

An RF transformer (Figure 6) provides an excellent solution to convert a single-ended source signal to a fully-differential signal, required by the MAX1180 for optimum performance. Connecting the center tap of the transformer to COM provides a $V_{\text{DD}}/2$ DC level shift to the input. Although a 1:1 transformer is shown, a step-up transformer may be selected to reduce the drive requirements. A reduced signal swing from the input driver, such as an op amp, may also improve the overall distortion.

In general, the MAX1180 provides better SFDR and THD with fully-differential input signals, than a single-ended drive, especially for high input frequencies. In differential input mode, even-order harmonics are lower as both inputs (INA+, INA- and/or INB+, INB-) are bal-

Dual 10-Bit, 105Mps, +3.3V, Low-Power ADC with Internal Reference and Parallel Outputs

MAX1180

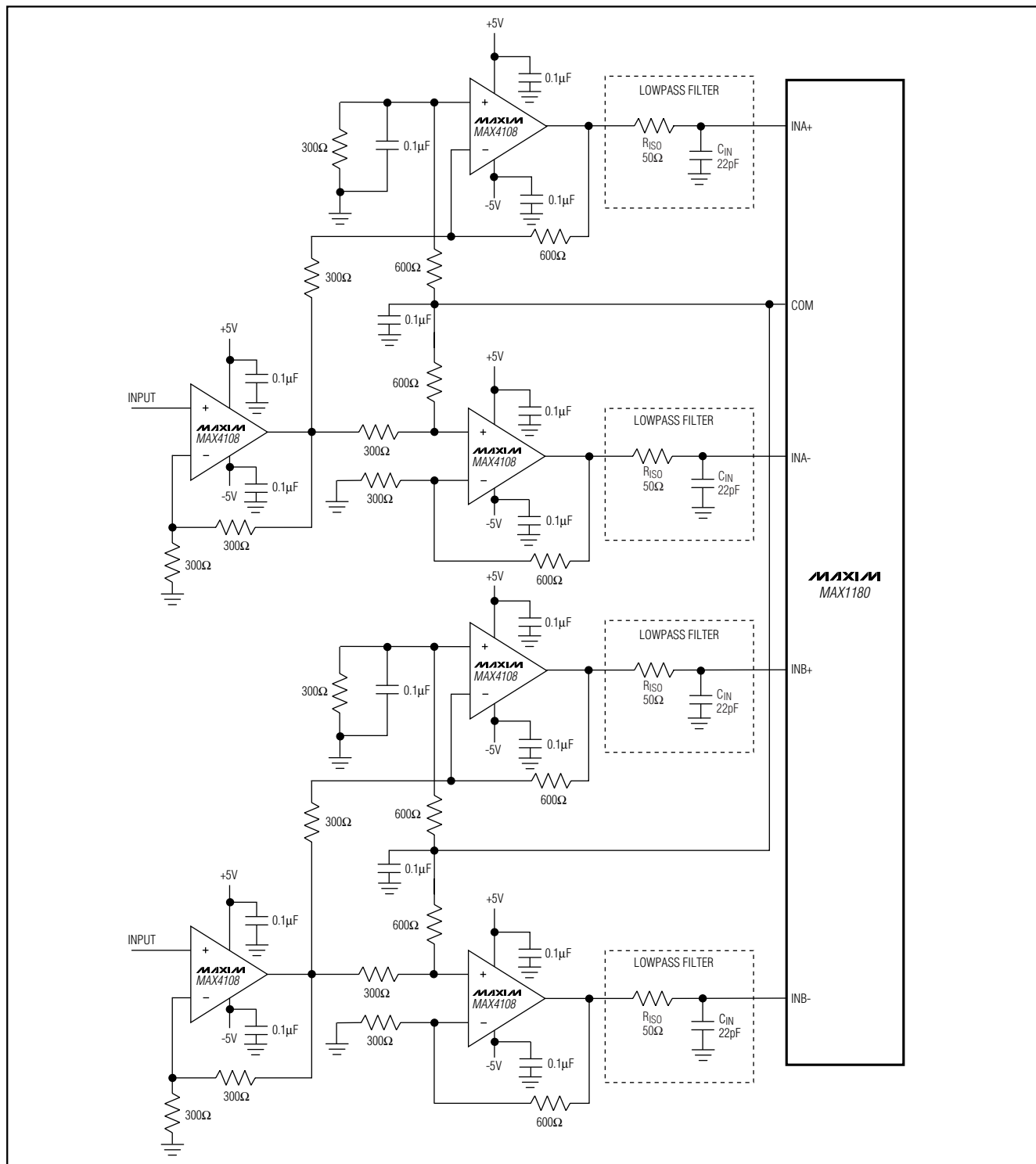


Figure 5. Typical Application for Single-Ended to Differential Conversion

Dual 10-Bit, 105Msps, +3.3V, Low-Power ADC with Internal Reference and Parallel Outputs

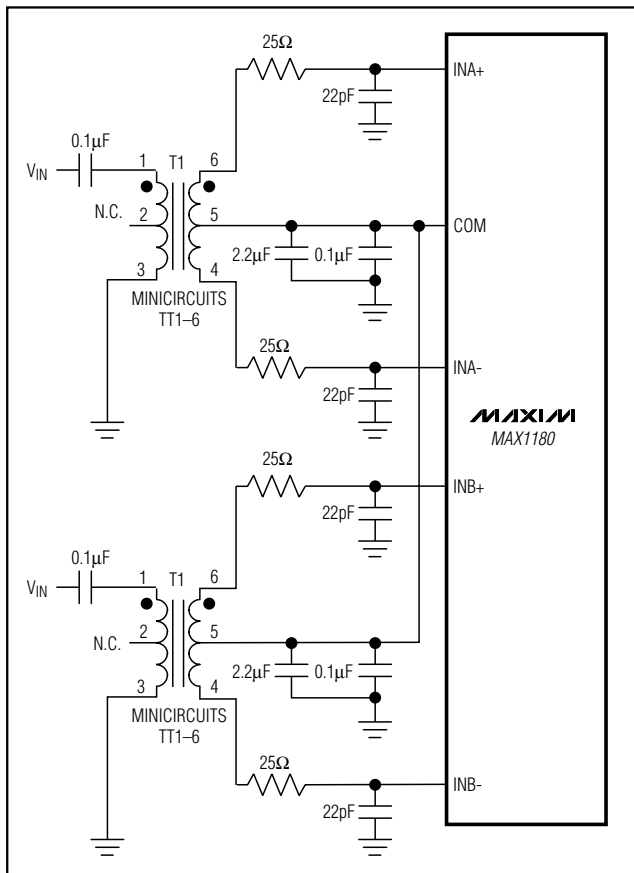


Figure 6. Transformer-Coupled Input Drive

anced, and each of the ADC inputs only require half the signal swing compared to single-ended mode.

Single-Ended AC-Coupled Input Signal

Figure 7 shows an AC-coupled, single-ended application. Amplifiers, like the MAX4108, provide high-speed, high bandwidth, low-noise, and low distortion to maintain the integrity of the input signal.

Typical QAM Demodulation Application

The most frequently used modulation technique for digital communications application is the Quadrature Amplitude Modulation (QAM). QAMs are typically found in spread-spectrum based systems. A QAM signal represents a carrier frequency modulated in both amplitude and phase. At the transmitter, modulating the baseband signal with quadrature outputs, a local oscil-

lator followed by subsequent up-conversion can generate the QAM signal. The result is an in-phase (I) and a quadrature (Q) carrier component, where the Q component is 90 degrees phase-shifted with respect to the in-phase component. At the receiver, the QAM signal is divided down into its I and Q components, essentially representing the modulation process reversed. Figure 8 displays the demodulation process performed in the analog domain, using the dual-matched, +3V, 10-bit ADCs, MAX1180 and the MAX2451 quadrature demodulators, to recover and digitize the I and Q baseband signals. Before being digitized by the MAX1180, the mixed-down signal components may be filtered by matched analog filters, such as Nyquist or Pulse-Shaping filters which remove any unwanted images from the mixing process, enhances the overall signal-to-noise (SNR) performance, and minimizes intersymbol interference.

Grounding, Bypassing, and Board Layout

The MAX1180 requires high-speed board layout design techniques. Locate all bypass capacitors as close to the device as possible, preferably on the same side as the ADC, using surface-mount devices for minimum inductance. Bypass V_{DD} , REFP, REFN, and COM with two parallel 0.1µF ceramic capacitors and a 2.2µF bipolar capacitor to GND. Follow the same rules to bypass the digital supply (OV_{DD}) to OGND. Multilayer boards with separate ground and power planes, produce the highest level of signal integrity. Consider the use of a split ground plane arranged to match the physical location of the analog ground (GND) and the digital output driver ground (OGND) on the ADCs package. The two ground planes should be joined at a single point, such that the noisy digital ground currents do not interfere with the analog ground plane. The ideal location of this connection can be determined experimentally at a point along the gap between the two ground planes, which produces optimum results. Make this connection with a low-value, surface-mount resistor (1Ω to 5Ω), a ferrite bead, or a direct short. Alternatively, all ground pins could share the same ground plane, if the ground plane is sufficiently isolated from any noisy, digital systems ground plane (e.g., downstream output buffer or DSP ground plane). Route high-speed digital signal traces away from the sensitive analog traces of either channel. Make sure to isolate the analog input lines to each respective converter to

Dual 10-Bit, 105Mps, +3.3V, Low-Power ADC with Internal Reference and Parallel Outputs

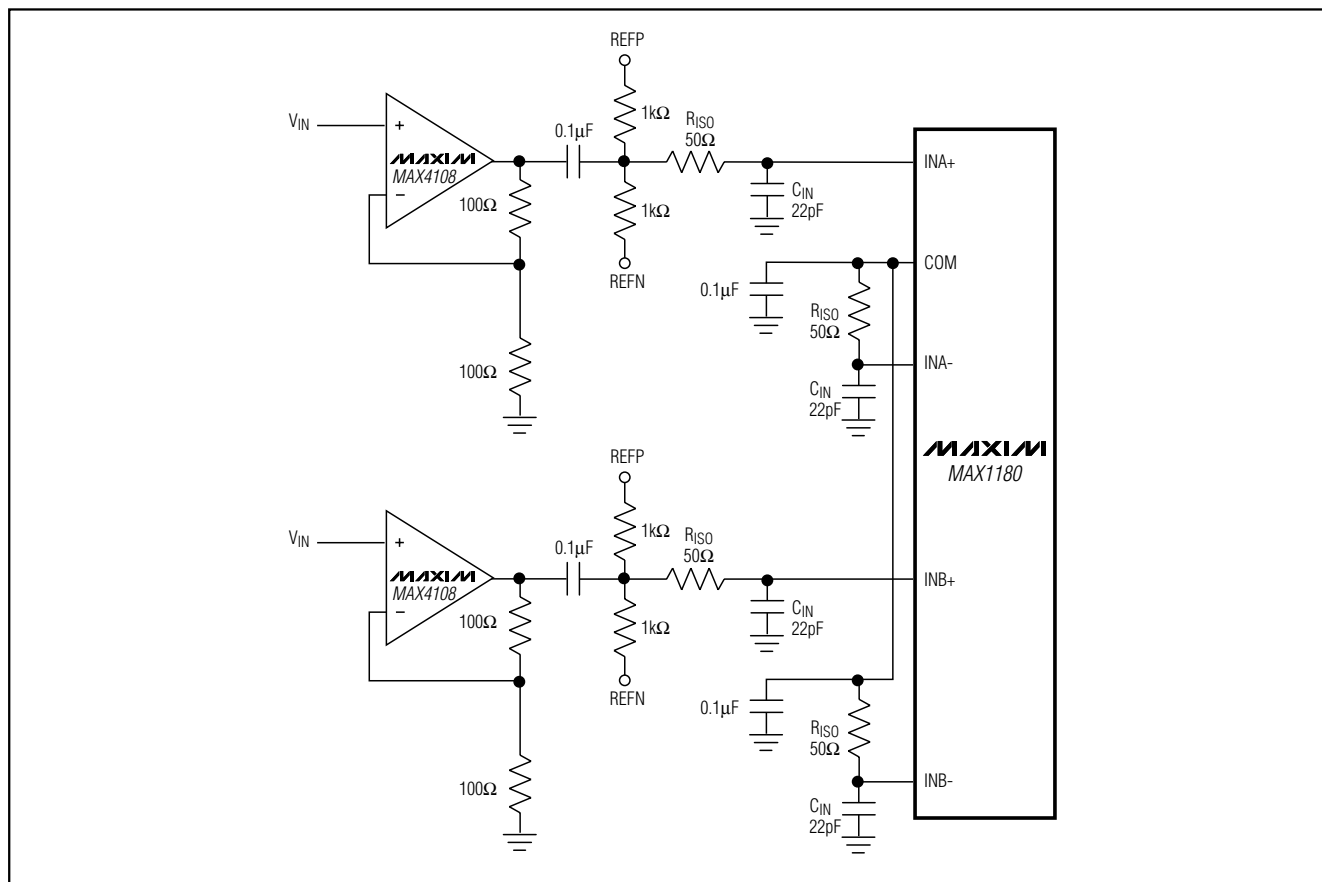


Figure 7. Using an Op Amp for Single-Ended, AC-Coupled Input Drive

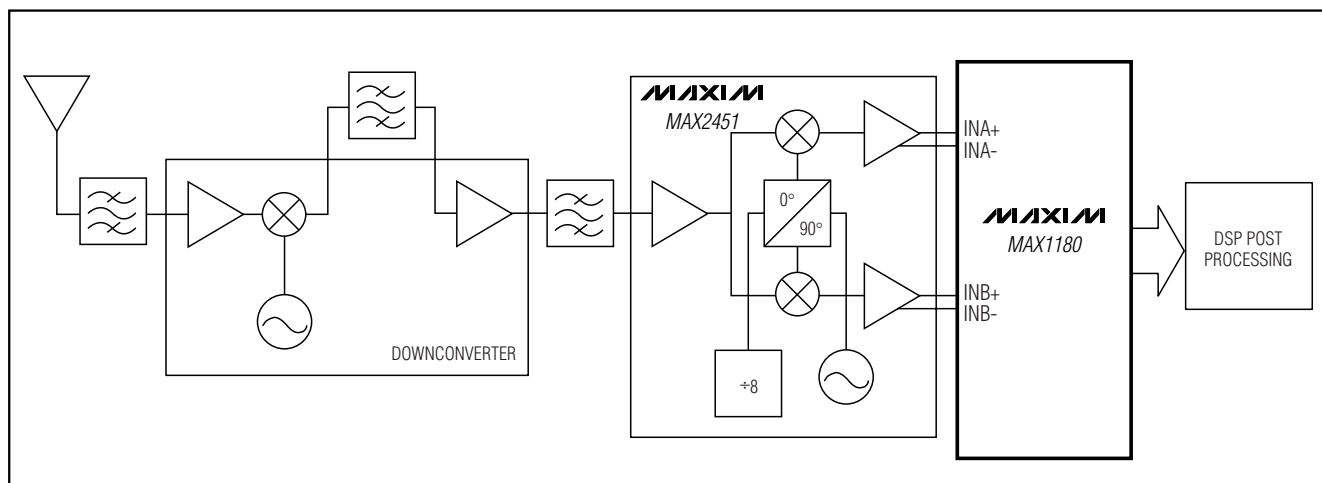


Figure 8. Typical QAM Application, Using the MAX1180

Dual 10-Bit, 105Msps, +3.3V, Low-Power ADC with Internal Reference and Parallel Outputs

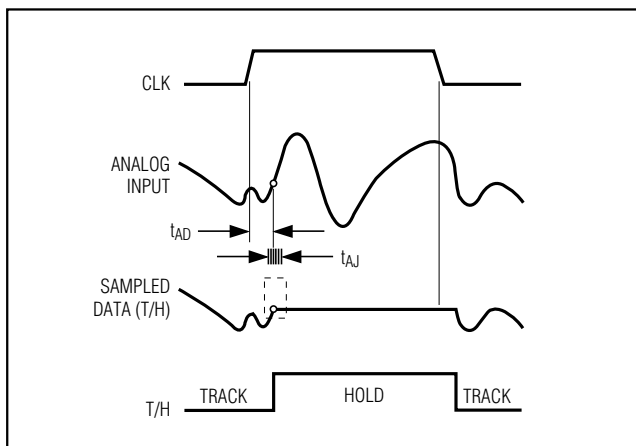


Figure 9. T/H Aperture Timing

minimize channel-to-channel crosstalk. Keep all signal lines short and free of 90 degree turns.

Static Parameter Definitions

Integral Nonlinearity (INL)

Integral nonlinearity is the deviation of the values on an actual transfer function from a straight line. This straight line can be either a best straight-line fit or a line drawn between the endpoints of the transfer function, once offset and gain errors have been nullified. The static linearity parameters for the MAX1180 are measured using the best straight-line fit method.

Differential Nonlinearity (DNL)

Differential nonlinearity is the difference between an actual step-width and the ideal value of 1LSB. A DNL error specification of less than 1LSB guarantees no missing codes and a monotonic transfer function.

Dynamic Parameter Definitions

Aperture Jitter

Figure 9 depicts the aperture jitter (t_{AJ}), which is the sample-to-sample variation in the aperture delay.

Aperture Delay

Aperture delay (t_{AD}) is the time defined between the falling edge of the sampling clock and the instant when an actual sample is taken (Figure 9).

Signal-to-Noise Ratio (SNR)

For a waveform perfectly reconstructed from digital samples, the theoretical maximum SNR is the ratio of the full-scale analog input (RMS value) to the RMS quantization error (residual error).

The ideal, theoretical minimum analog-to-digital noise is caused by quantization error only and results directly from the ADCs resolution (N-Bits):

$$SNR_{dB[max]} = 6.02dB \times N + 1.76dB$$

In reality, there are other noise sources besides quantization noise; thermal noise, reference noise, clock jitter, etc. SNR is computed by taking the ratio of the RMS signal to the RMS noise, which includes all spectral components minus the fundamental, the first five harmonics, and the DC offset.

Signal-to-Noise Plus Distortion (SINAD)

SINAD is computed by taking the ratio of the RMS signal to all spectral components minus the fundamental and the DC offset.

Effective Number of Bits (ENOB)

ENOB specifies the dynamic performance of an ADC at a specific input frequency and sampling rate. An ideal ADC's error consists of quantization noise only. ENOB is computed from:

$$ENOB = \frac{SINAD_{dB} - 1.76dB}{6.02dB}$$

Total Harmonic Distortion (THD)

THD is typically the ratio of the RMS sum of the first four harmonics of the input signal to the fundamental itself. This is expressed as:

$$THD = 20 \times \log_{10} \left(\frac{\sqrt{V_2^2 + V_3^2 + V_4^2 + V_5^2}}{V_1} \right)$$

where V_1 is the fundamental amplitude, and V_2 through V_5 are the amplitudes of the 2nd- through 5th-order harmonics.

Spurious-Free Dynamic Range (SFDR)

SFDR is the ratio expressed in decibels of the RMS amplitude of the fundamental (maximum signal component) to the RMS value of the next largest spurious component, excluding DC offset.

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Intermodulation Distortion (IMD)

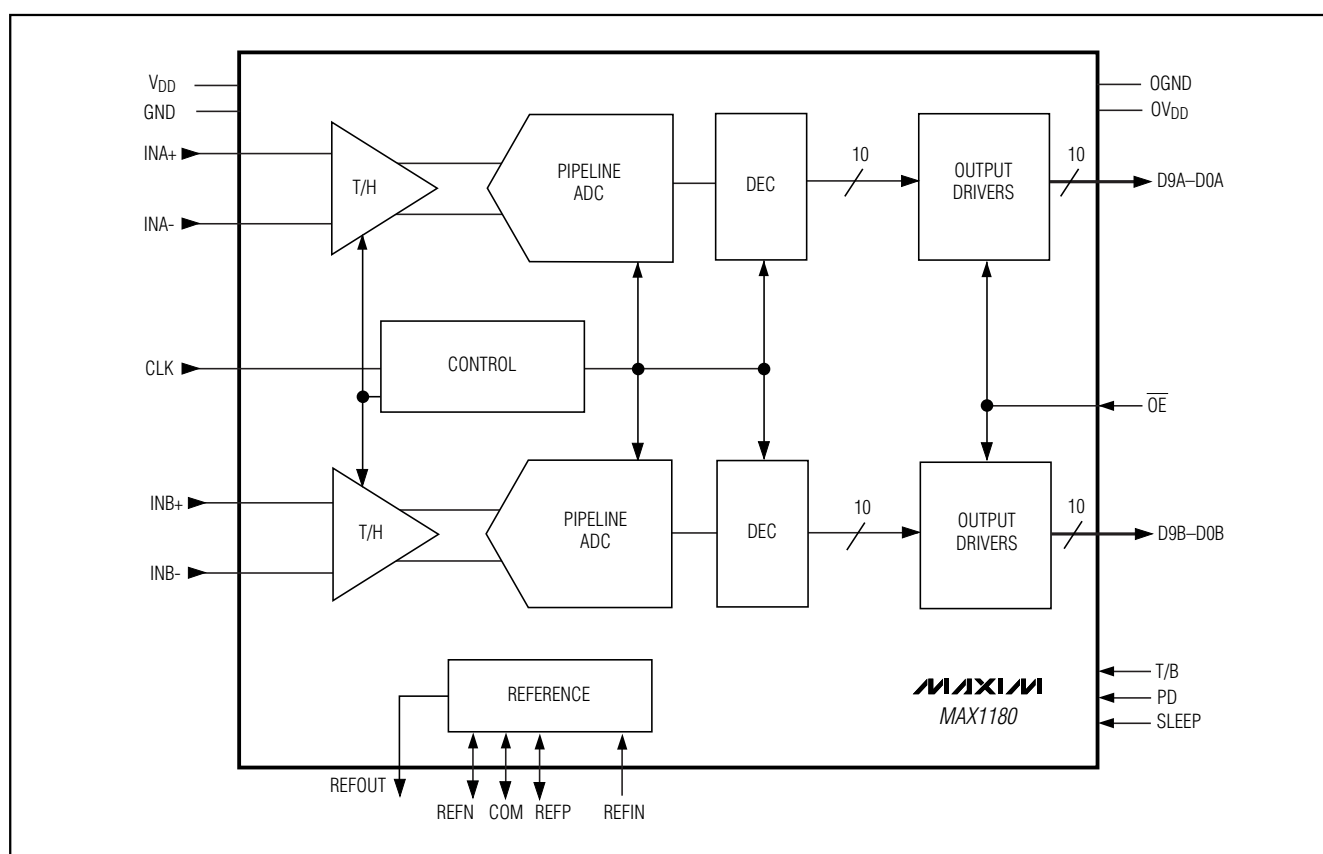
The two-tone IMD is the ratio expressed in decibels of either input tone to the worst 3rd-order (or higher) intermodulation products. The individual input tone levels are at -6.5dB full scale and their envelope is at -0.5dB full scale.

Chip Information

TRANSISTOR COUNT: 10,811

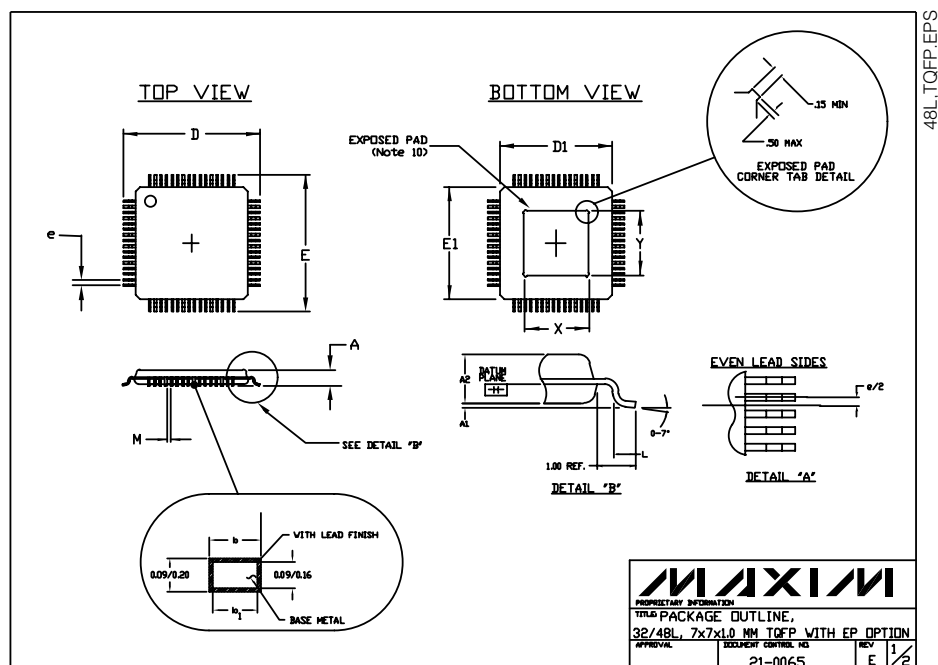
PROCESS: CMOS

Functional Diagram



Dual 10-Bit, 105Msps, +3.3V, Low-Power ADC with Internal Reference and Parallel Outputs

Package Information

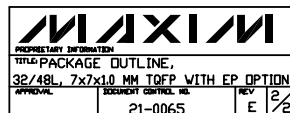


481 TOFP FPS

- NOTES:
1. ALL DIMENSIONS AND TOLERANCING CONFORM TO ANSI Y14.5-1982.
 2. DATUM PLANE  IS LOCATED AT MOLD PARTING LINE AND COINCIDENT WITH LEAD, WHERE LEAD EXISTS.
 3. PLASTIC BODY AT BOTTOM OF PARTING LINE.
 4. DIMENSIONS DI AND EI DO NOT INCLUDE MOLD PROTRUSION.
 5. ALLOWED PROTRUSION IS 0.005 MM ON DI AND EI DIMENSIONS.
 6. THE TOP OF PACKAGE IS SMALLER THAN THE BOTTOM OF PACKAGE BY 0.15 MILLIMETERS.
 7. DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 MM TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.
 8. MOLDING DIMENSION MILLIMETER.
 9. THIS OUTLINE CONFORMS TO JEDEC PUBLICATION 95 REGISTRATION MQ-136, VARIATIONS AC AND AE.
 10. LEADS SHALL BE COPLANAR WITHIN .004 INCH.
 11. EXPOSED DIE PAD SHALL BE COPLANAR WITH BOTTOM OF PACKAGE WITHIN 2 MILS (.05 MM).
 12. APPLICATION TO EXPOSED PAD (EP) VERSIONS ONLY. SEE INDIVIDUAL PRODUCT SPECIFICATION FOR PRODUCT USE, PACKAGE USE, AND PACKAGE MARKING.

SYMBOL	JEDEC VARIATION					
	ALL DIMENSIONS IN MILLIMETERS					
	AC			AE		
	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
A	<u>0.05</u>	<u>0.10</u>	1.20	<u>0.05</u>	<u>0.10</u>	1.20
A ₁	0.05	0.10	0.15	0.05	0.10	0.15
A ₂	0.95	1.00	1.05	0.95	1.00	1.05
D	9.00 BSC.			9.00 BSC.		
D ₁	7.00 BSC.			7.00 BSC.		
E	9.00 BSC.			9.00 BSC.		
E ₁	7.00 BSC.			7.00 BSC.		
L	0.45	0.60	0.75	0.45	0.60	0.75
M	0.15	<u>0.15</u>	<u>0.15</u>	0.14	<u>0.14</u>	<u>0.14</u>
N	32			48		
n	0.60 BSC.			0.50 BSC.		
b	0.30	0.37	0.45	0.17	0.22	0.27
b ₁	0.30	0.35	0.40	0.17	0.20	0.23
W _K	3.20	3.50	3.80	3.70	4.00	4.30
W _V	3.20	3.50	3.80	3.70	4.00	4.30

* EXPOSED PAD
(Note 10)



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